

Simulation of Streaking Experiments at Surfaces

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Coworkers (Theory)



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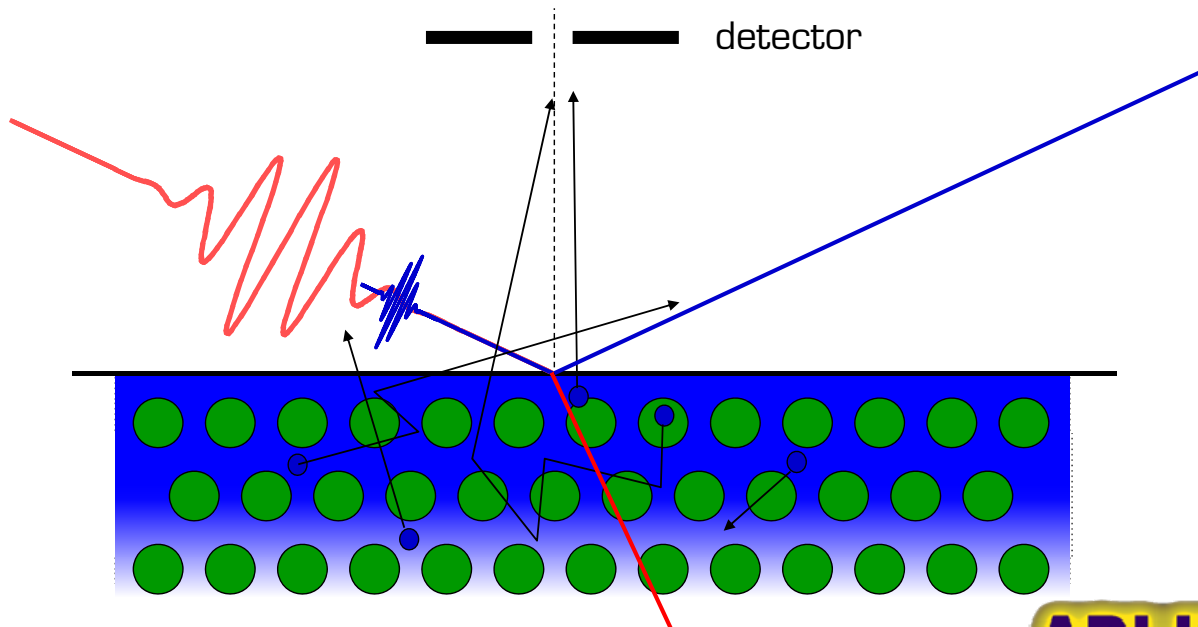
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Simulated System

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Outline

- Review of Simulation Methods
- Classical-Transport Model
 - Electron excitation by XUV pulse
 - depth and energy distribution of excited electrons
 - delayed excitation of inner shell electrons?
 - Transport of electrons in metals
 - elastic and inelastic scattering processes
 - dielectric function
- Comparison to experimental results
- Summary – Outlook

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Methods

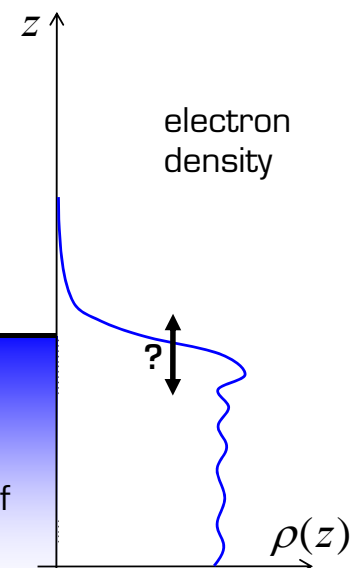
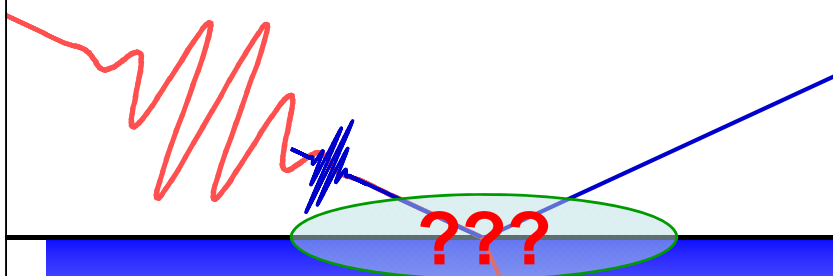
- Delay due to crystal structure
 - Cavalieri et al.: dispersion relation perpendicular to surface (Bragg scattering)
 - Zhang and Thumm: “structure factor” for core electrons, jellium for CB electrons + fitting to experimental result
- Delay due to transport
 - Baggesen and Madsen: Boltzmann transport equation, anisotropy due to surface neglected
 - Kazansky and Echenique: wave function propagation of core and CB electrons; delay due to interaction with (shielded) core hole (presentation later today)
 - Lemell et al.: classical transport

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Combined XUV and IR fields

$\lambda = 702 \text{ nm}$
 $n_\lambda = 3.85 \rightarrow \theta = 75.5^\circ$
 $n_{\text{XUV}} = 0.93 \rightarrow \text{total reflection}$

$$\varepsilon = \varepsilon_1 + i\varepsilon_2 = (n^2 - k^2) + i 2nk$$



sharp edge: \rightarrow intensities decay to $I = I_0/e$ at a depth of
 ~17 atomic layers (XUV)
 ~87 atomic layers (IR)

Classical Transport Simulation

primary electrons: $\left\{ \begin{array}{l} \bullet \text{ energy distribution} \\ \bullet \text{ depth of excitation} \\ \bullet \text{ angular distribution} \end{array} \right.$ (typically 10^7 trajectories)

$$\dot{\vec{p}} = \vec{F}_{NIR}(\vec{r}, t) + \vec{F}_{stoc}(t) + \vec{F}_{surf}(\vec{r})$$

deflection by
streaking field

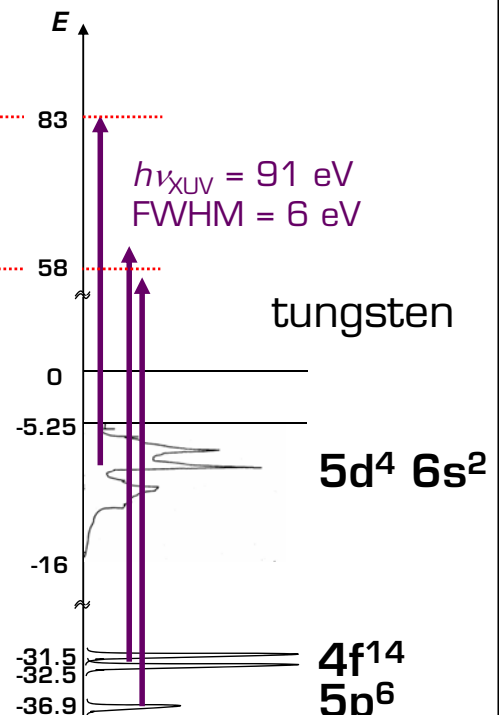
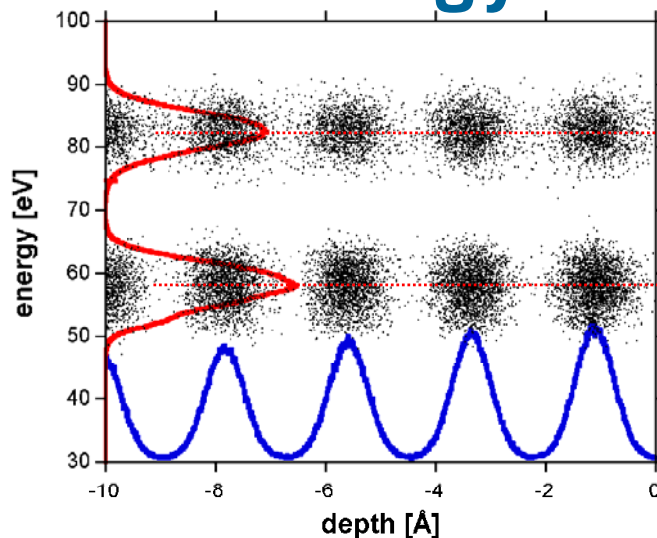
scattering at
- target cores (elastic)
- target electrons (inelastic)

deflection by
surface potential

transport of secondary electrons included
→ particle number not conserved

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Energy distribution

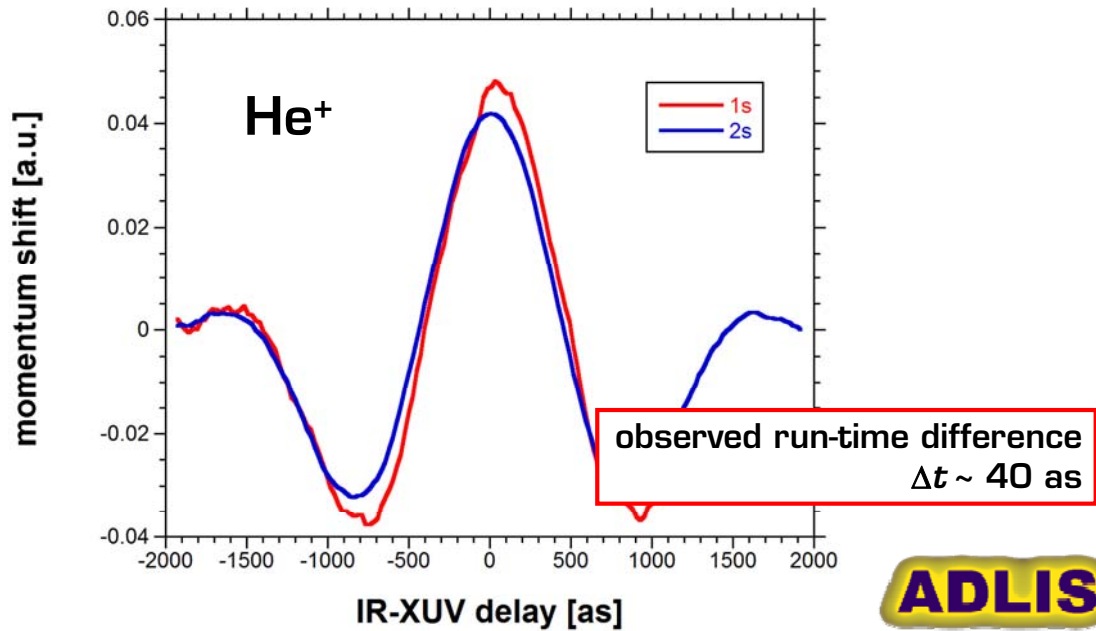


evanescent wave: $I \sim \exp[-2\kappa z]$
 $\kappa \sim 0.013/\text{Å} \sim 17$ atomic layers

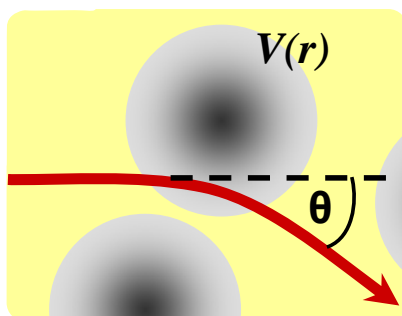
tungsten:
 $a = 3.16 \text{ Å}$
 $d_{(110)} = 2.24 \text{ Å}$

Excitation delay?

Experiments with Ne → observed delay for different n, ℓ



Electron transport



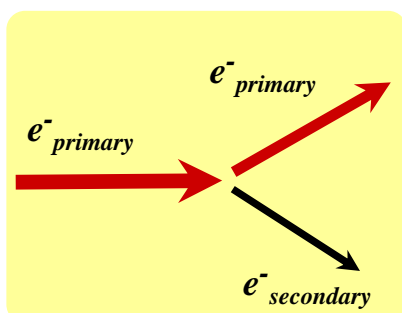
elastic scattering:

muffin-tin potentials for W atoms

partial wave expansion

→ doubly differential

scattering cross section



inelastic scattering:

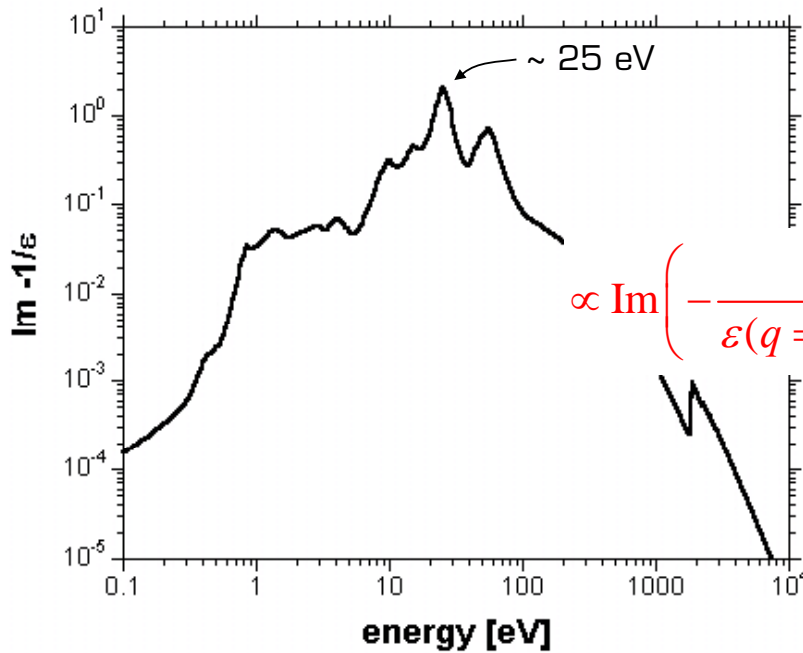
from dielectric function

→ inelastic mean free path

$$E'_{prim} = E_{prim} - \Delta E$$

$$E_{sec} = \Delta E$$

Energy loss



optical data for W

loss function:

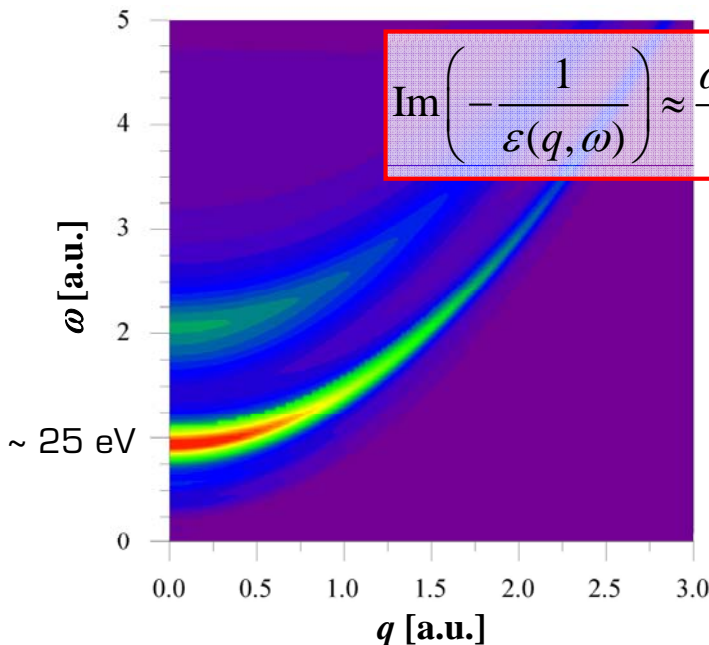
$$\propto \text{Im} \left(-\frac{1}{\varepsilon(q=0, \omega)} \right) = \text{Im} \left(-\frac{1}{\varepsilon_{opt}(\omega)} \right)$$

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Dielectric function for W

extrapolation of optical data to q - ω plane



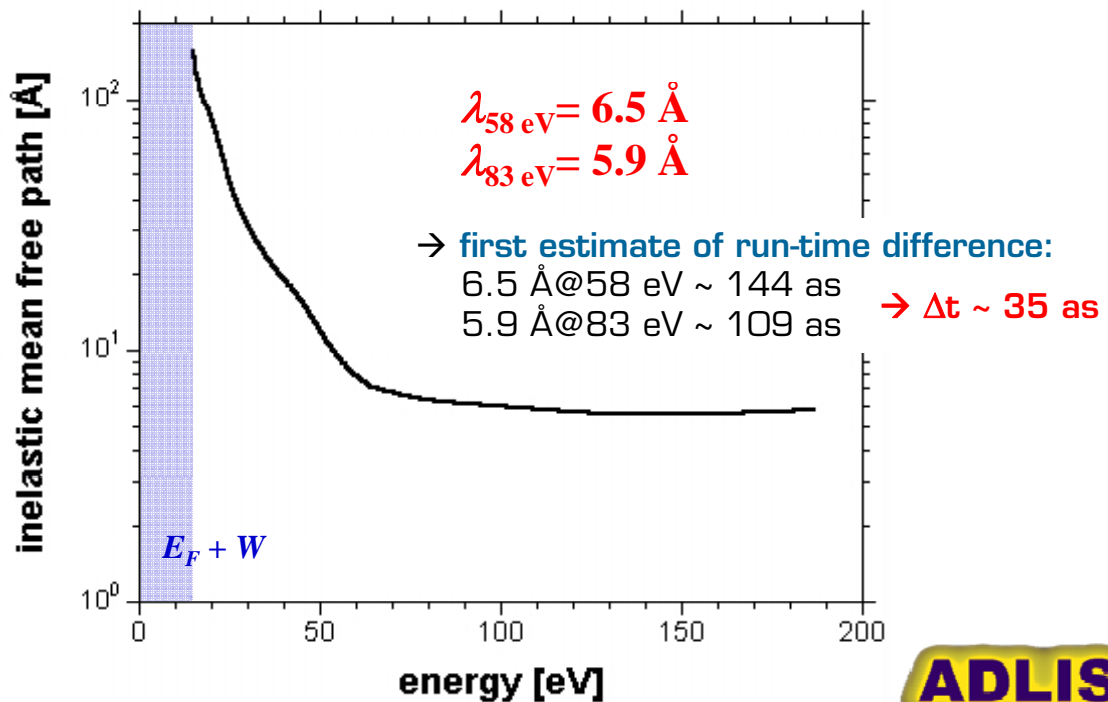
$$\text{Im} \left(-\frac{1}{\varepsilon(q, \omega)} \right) \approx \frac{\omega - q^2/2}{\omega} \text{Im} \left(-\frac{1}{\varepsilon_{opt}(\omega - q^2/2)} \right)$$

neglects creation of
electron-hole pairs;
good approximation for
electron energies $E \gg \omega_p \sim 25$ eV

$$\frac{d^2 \lambda_{inel}^{-1}}{dq d\omega} \propto \text{Im} \left(-\frac{1}{\varepsilon(q, \omega)} \right)$$

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Inelastic mean free path



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Streaking

streaking field: $E(t) = E_0 \sin^2[t\pi / 2\tau] \cos[\omega_{NIR}(t - \tau)]$

momentum change
within target:

$$\Delta p = \int_{t_{start}}^{t_{escape}} E(t) dt$$

almost perpendicular to
observation direction, Δt much
shorter than oscillation period
→ small sub-surface contribution

momentum change
after escape:

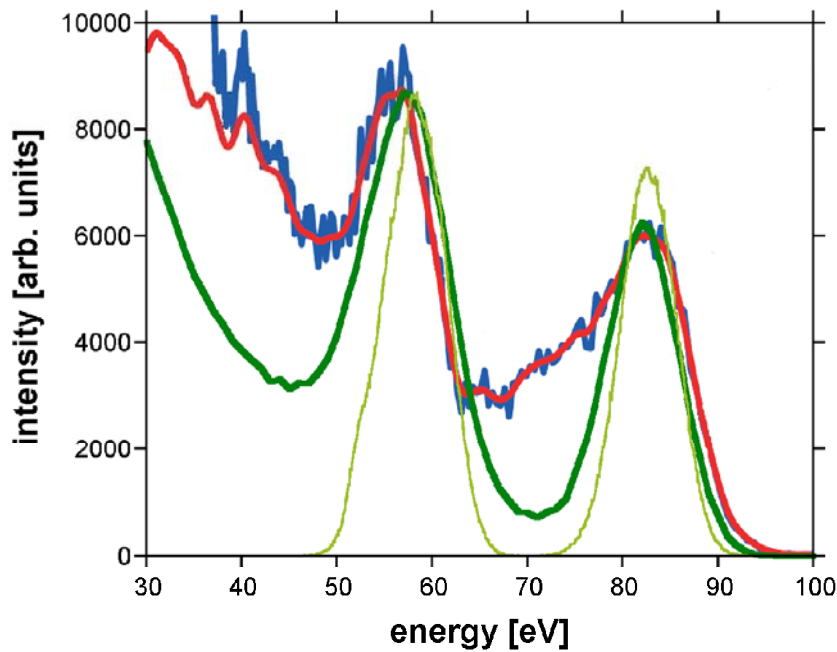
$$\Delta p = \int_{t_{escape}}^{\infty} E(t) dt$$

parameters:

- XUV-pulse: FWHM $\tau_{XUV} \sim 300 \text{ as}$ (defines t_{start})
- streaking laser wavelength $\lambda = 702 \text{ nm}$
- FWHM $\tau_{NIR} = 5.7 \text{ fs}$
- $I = 2 \times 10^{12} \text{ W/cm}^2 \rightarrow E_0 = 0.075 \text{ a.u.}$

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Electron energy spectra



maximum of XUV pulse
at start of NIR pulse;
free electron disp. rel.

experiment:

[raw spectrum](#)

[smoothed spectrum](#)

simulation:

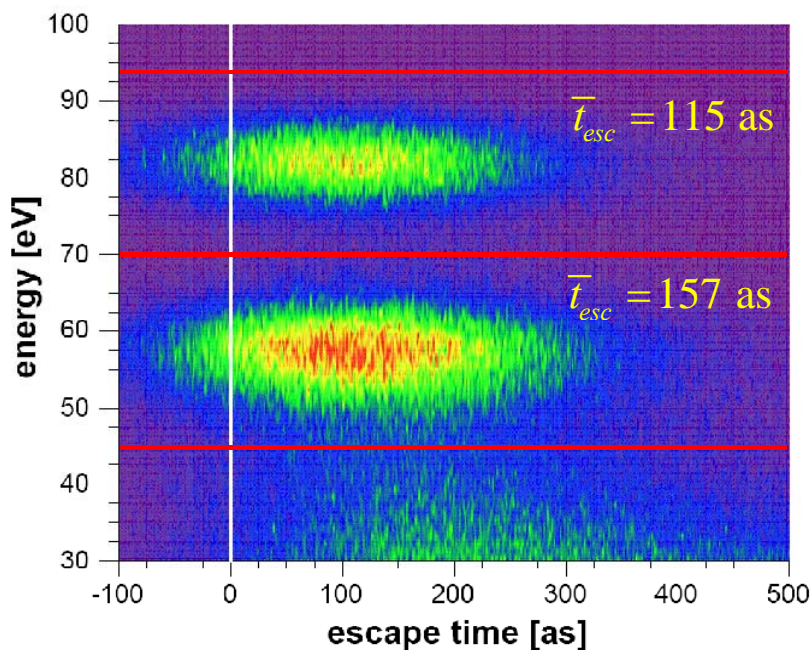
[excitation spectrum](#)

[energy spectrum of](#)

[escaped electrons](#)

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Escape time of electrons

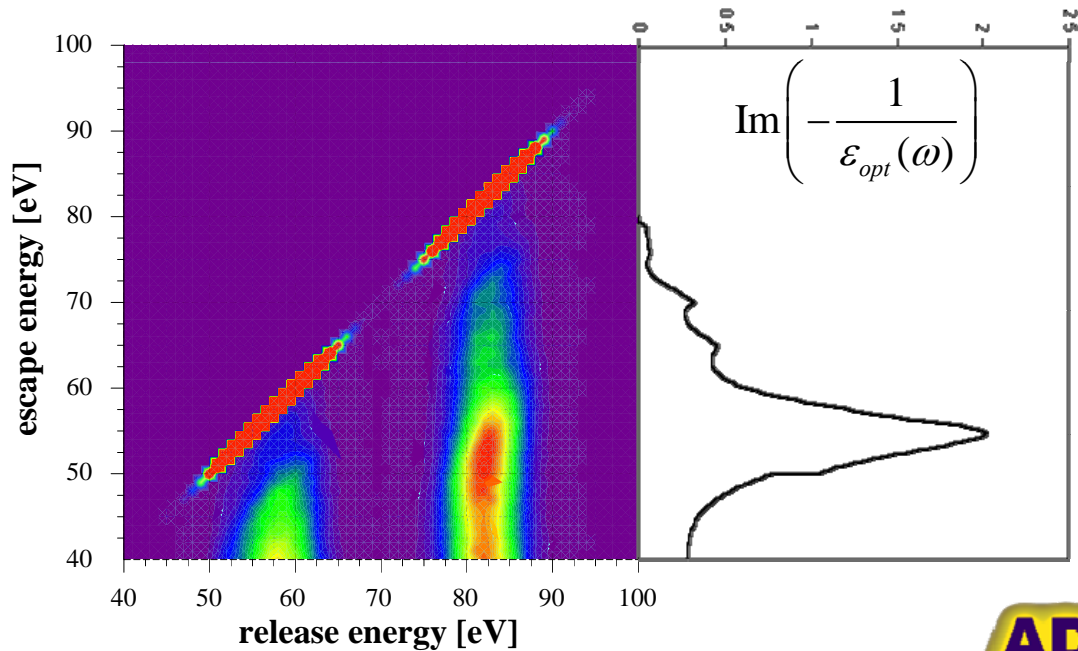


maximum of XUV
pulse at $t = 0$

run-time difference:
 $\Delta t = 42$ as

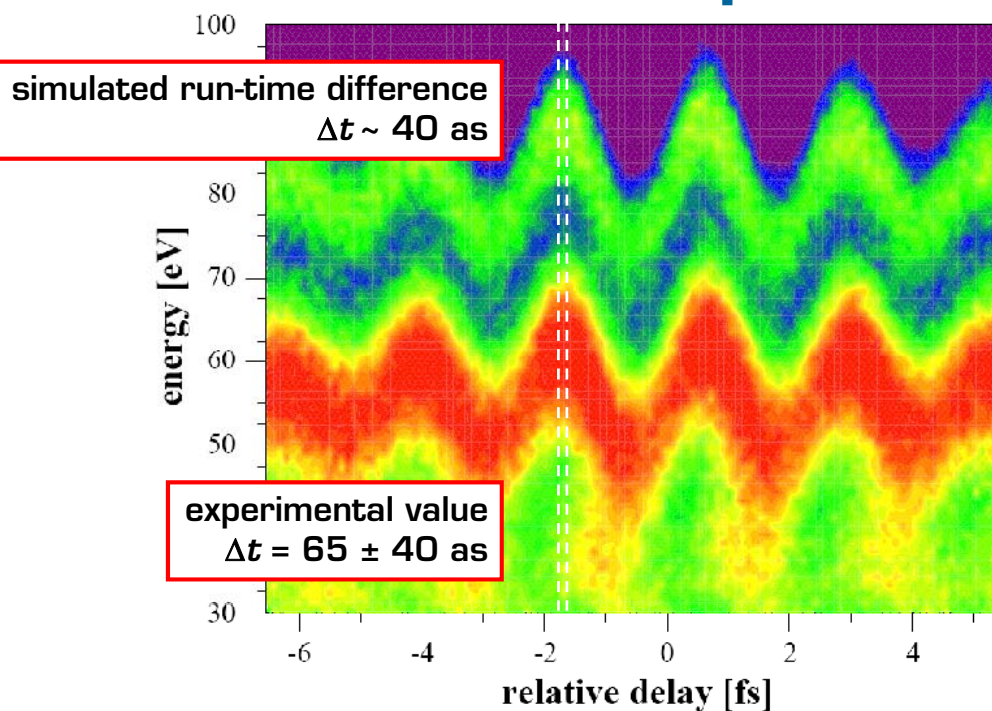
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Energy loss and delay



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Streaked spectra



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Other materials

theorists choice: Al target; Mg experiments in preparation

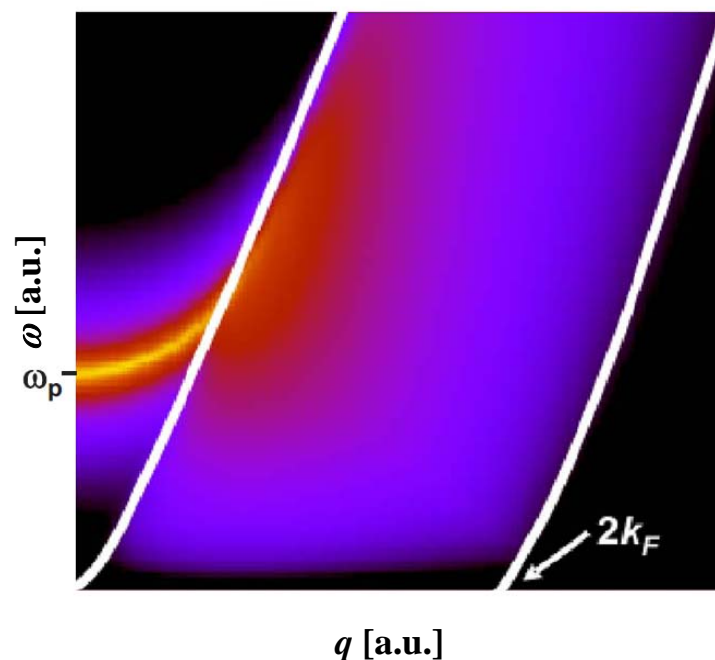
advantages: - (almost) free electron gas
- strong plasmon loss
- deeply bound core electrons

disadvantage: hard to clean (AlO-layer)

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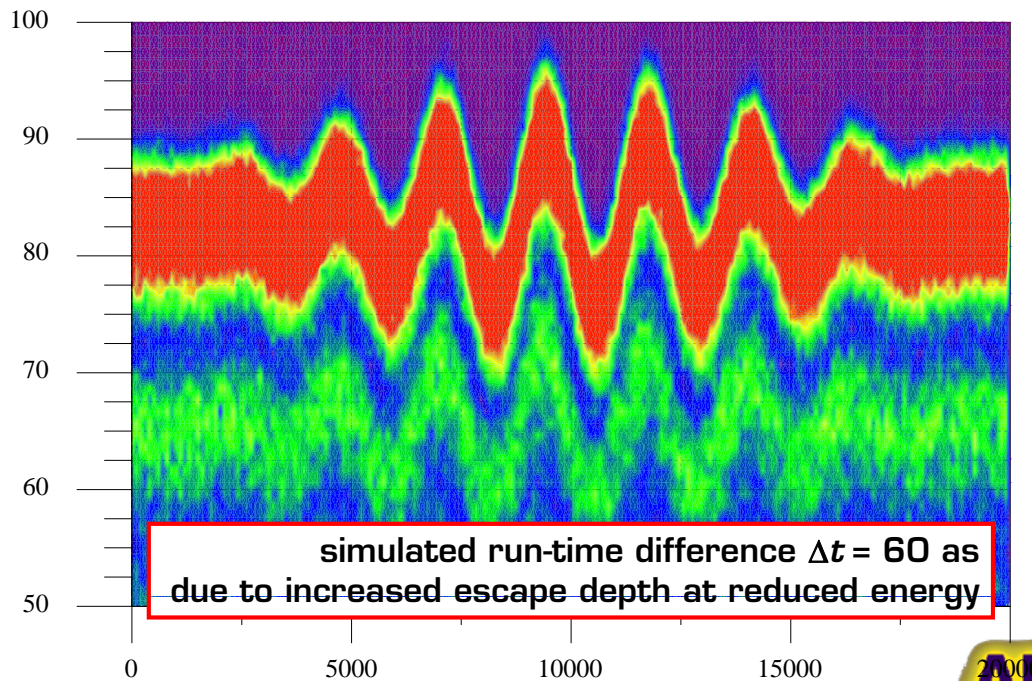
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Dielectric function of Al



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Streaking of AI



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Summary

- Various models for photoelectron streaking at surfaces
- Classical transport model
 - good agreement with measured energy spectra
 - delayed emission of deeply bound electrons?
- Simulated run-time difference too small

Remaining differences

- Intrinsic delay for core electrons?
- Crystal effect on excitation and transport?
- Localized surface induced fields?

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